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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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DMJT9435

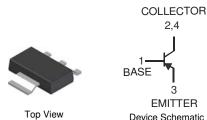
LOW V_{CE(SAT)} PNP SURFACE MOUNT TRANSISTOR

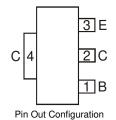
Features

- Ideally Suited for Automated Assembly Processes
- Low Collector-Emitter Saturation Voltage
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.115 grams (approximate)





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-45	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-6	V
Peak Pulse Current	I _{CM}	-5	Α
Continuous Collector Current	Ic	-3	Α
Continuous Base Current	I _B	-1	Α

Device Schematic

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1.2	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{\theta JA}$	104	°C/W
Power Dissipation (Note 4) @ T _A = 25°C	P _D	2	W
Thermal Resistance, Junction to Ambient Air (Note 4) @ T _A = 25°C	$R_{\theta JA}$	62.5	°C/W
Power Dissipation @ T _C = 25°C	PD	3	W
Thermal Resistance, Junction to Case @ T _C = 25°C	$R_{\theta JA}$	42	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on FR-4 PCB with minimum recommended pad layout.
 Device mounted on FR-4 PCB with 1 inch² copper pad layout.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage (Note 5)	V _{(BR)CEO}	-30	_		V	$I_C = -10 \text{mA}$	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-6	_		٧	$I_E = -50\mu A$	
		_	_	-20	μА	$V_{CB} = -25V$, $R_{BE} = 200\Omega$	
Collector-Base Cutoff Current	I _{CER}	_		-200	μА	$V_{CB} = -25V, R_{BE} = 200\Omega,$ $T_A = 125^{\circ}C$	
Emitter-Base Cutoff Current	I _{EBO}	_	_	-10	μА	$V_{EB} = -5V, I_C = 0$	
ON CHARACTERISTICS (Note 5)					•	-	
		125	_	_		$V_{CE} = -1V, I_{C} = -0.8A$	
DC Current Gain	h _{FE}	110	_	_	_	$V_{CE} = -1V, I_{C} = -1.2A$	
		90	_	_		$V_{CE} = -1V, I_{C} = -3A$	
		_	-100	-210		I _C = -0.8A, I _B = -20mA	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	-275	mV	$I_C = -1.2A$, $I_B = -20mA$	
		_	-250	-550		$I_C = -3A$, $I_B = -300mA$	
Equivalent On-Resistance	R _{CE(SAT)}	_	83	183	mΩ	$I_C = -3.0A$, $I_B = -300mA$	
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	_	-1.25	٧	$I_C = -3A$, $I_B = -300mA$	
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_	_	-1.1	V	$V_{CE} = -4V, I_{C} = -1.2A$	
SMALL SIGNAL CHARACTERISTICS							
Transition Frequency	f⊤	_	160	_	MHz	$V_{CE} = -10V, I_{C} = -100mA,$ f = 100MHz	
Output Capacitance	C _{obo}	_	45	150	pF	V _{CB} = -10V, f = 1MHz	
Input Capacitance	C _{ibo}	_	140	_	рF	$V_{EB} = -8V$, $f = 1MHz$	
SWITCHING CHARACTERISTICS							
Turn-On Time	t _{on}	_	200	_	ns	V _{CC} = -15V, I _C = -1.2A, I _{B1} = -20mA	
Delay Time	t _d	_	90		ns		
Rise Time	t _r	_	110	_	ns	IB1 = -ZUIIIA	
Turn-Off Time	t _{off}		155	_	ns	V _{CC} = -15V, I _C = -1.2A, I _{B1} = I _{B2} = -20mA	
Storage Time	ts	_	100	_	ns		
Fall Time	t _f		55	_	ns		

Notes: 5. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

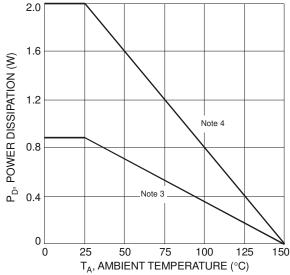


Fig. 1 Power Dissipation vs. Ambient Temperature

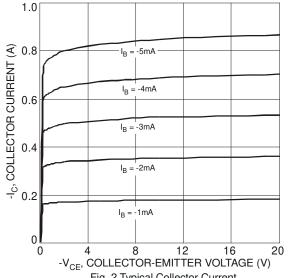
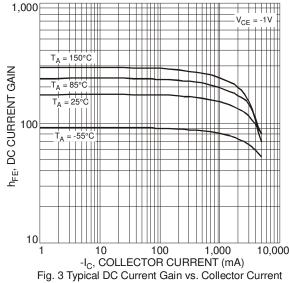
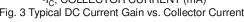
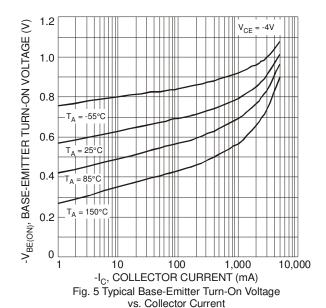


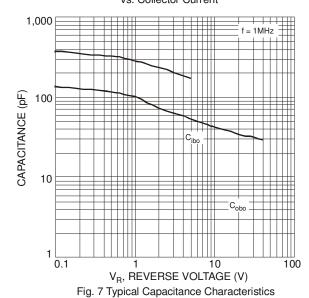
Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

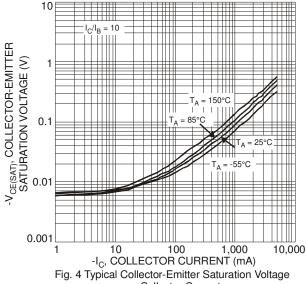












vs. Collector Current

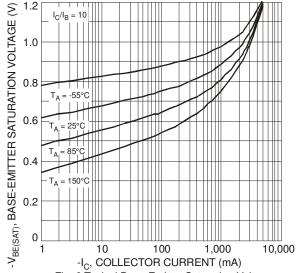


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

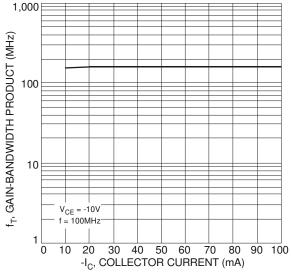


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

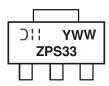


Ordering Information (Note 6)

Part Number	Case	Packaging
DMJT9435-13	SOT-223	2500/Tape & Reel

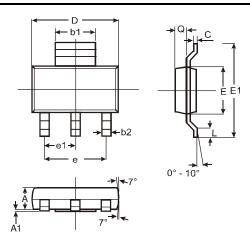
Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



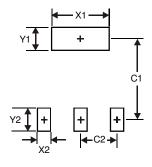
ZPS33 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex: 8 = 2008) WW = Week code 01 - 52

Package Outline Dimensions



SOT-223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A 1	0.010	0.15	0.05	
b1	2.90	3.10	3.00	
b2	0.60	0.80	0.70	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	_	_	4.60	
e1		_	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

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